

Vishay Semiconductors

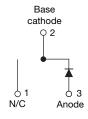
HEXFRED[®], **Ultrafast Soft Recovery Diode, 15 A**

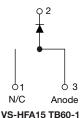




TO-263AB (D²PAK)

TO-262AA





VS-HFA15 TB60SPbF

| 01 | 03 |
|--------|--------------|
| N/C | Anode |
| S-HFA1 | 15 TB60-1PbF |

| PRODUCT SUMMARY | |
|----------------------------------|---|
| Package | TO-263AB (D ² PAK), TO-262AA |
| I _{F(AV)} | 15 A |
| V _R | 600 V |
| V _F at I _F | 1.2 V |
| t _{rr} (typ.) | 23 ns |
| T _J max. | 150 °C |
| Diode variation | Single die |

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{BBM} and Q_{rr}
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and gualified for industrial level
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | |
| Cathode to anode voltage | V _R | | 600 | V | | | | |
| Maximum continuous forward current | I _F | T _C = 100 °C | 15 | | | | | |
| Single pulse forward current | I _{FSM} | | 150 | А | | | | |
| Maximum repetitive forward current | I _{FRM} | | 60 | | | | | |
| Maximum power dissinction | р | T _C = 25 °C | 74 | W | | | | |
| Maximum power dissipation | P _D | T _C = 100 °C | 29 | vv | | | | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | -55 to +150 | °C | | | | |

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Document Number: 94054

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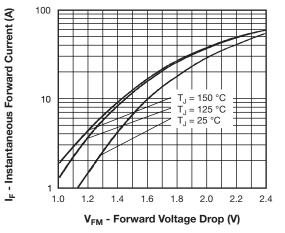
| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-----------------|--|-------------|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage | V _{BR} | I _R = 100 μA | | 600 | - | - | |
| | | I _F = 15 A | | - | 1.3 | 1.7 | V |
| Maximum forward voltage | V _{FM} | I _F = 30 A | See fig. 1 | - | 1.5 | 2.0 | |
| | | I _F = 15 A, T _J = 125 °C | | - | 1.2 | 1.6 | |
| Maximum reverse | 1 | $V_R = V_R$ rated | See fig. 2 | - | 1.0 | 10 | μA |
| leakage current | I _{RM} | $T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ | See lig. 2 | - | 400 | 1000 | μΑ |
| Junction capacitance | CT | V _R = 200 V | See fig. 3 | - | 25 | 50 | pF |
| Series inductance | LS | Measured lead to lead 5 mm from pa | ackage body | - | 8.0 | - | nH |

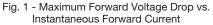
| DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified) | | | | | | | |
|---|---------------------------|---|--------------------------------|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CON | NDITIONS | MIN. | TYP. | MAX. | UNITS |
| D | t _{rr} | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ /}$ | ∿µs, V _R = 30 V | - | 23 | - | |
| Reverse recovery time See fig. 5 | t _{rr1} | T _J = 25 °C | | - | 50 | 60 | ns |
| dee lig. J | t _{rr2} | T _J = 125 °C | | - | 105 | 120 | |
| Peak recovery current | I _{RRM1} | T _J = 25 °C | I _F = 15 A | - | 4.5 | 6.0 | А |
| See fig. 6 | I _{RRM2} | T _J = 125 °C | | - | 6.5 | 10 | A |
| Reverse recovery charge | Q _{rr1} | T _J = 25 °C | dl _F /dt = 200 A/µs | - | 84 | 180 | nC |
| See fig. 7 | Q _{rr2} | T _J = 125 °C | V _R = 200 V | - | 241 | 600 | nc |
| Peak rate of fall of recovery current during t _b | dl _{(rec)M} /dt1 | T _J = 25 °C |] | - | 188 | - | A/µs |
| See fig. 8 | dl _{(rec)M} /dt2 | T _J = 125 °C | | - | 160 | - | Avµs |

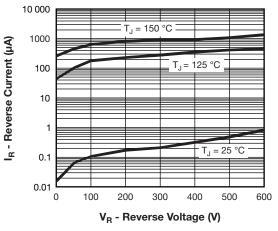
| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|-------------------|--|-------------|------|------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C | | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 1.7 | | | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 80 | K/W | | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | | | |
| Weight | | | - | 2.0 | - | g | | |
| weight | | | - | 0.07 | - | oz. | | |
| Marking davias | | Case style D ² PAK | HFA15TB60S | | | | | |
| Marking device | | Case style TO-262 | HFA15TB60-1 | | | | | |



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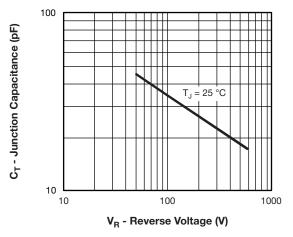
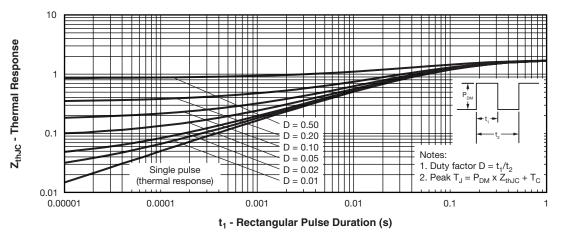


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage







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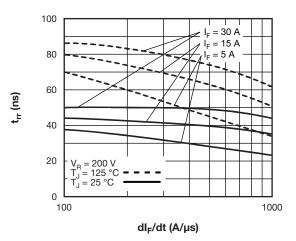


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

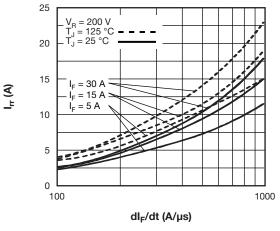


Fig. 6 - Typical Recovery Current vs. dl_F/dt

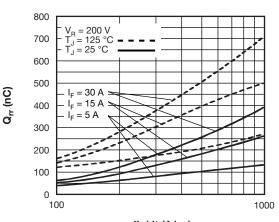




Fig. 7 - Typical Stored Charge vs. dl_F/dt

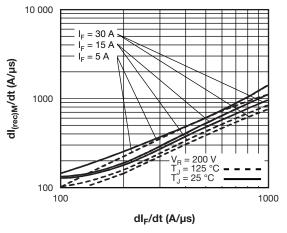


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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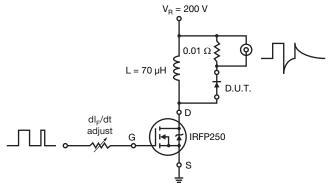


Fig. 9 - Reverse Recovery Parameter Test Circuit

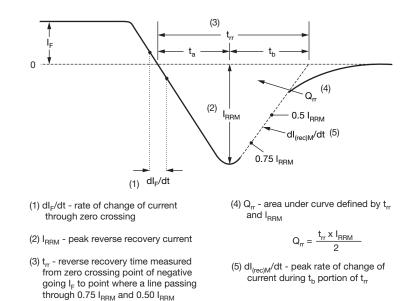


Fig. 10 - Reverse Recovery Waveform and Definitions

extrapolated to zero current.



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ORDERING INFORMATION TABLE

| Device code | VS- | HF | А | 15 | тв | 60 | S | TRL | PbF |
|-------------|-----|--------|---------------------|-----------------------|-----------|-----------|-----------------------|--------------------|----------|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 |
| | 1 . | · Visl | hay Sen | niconduc | ctors pro | oduct | | | |
| | 2 - | · HE | XFRED [@] | [®] family | | | | | |
| | 3 - | Ele | ctron irra | adiated | | | | | |
| | 4 | · Cur | rent rati | ng (15 = | = 15 A) | | | | |
| | 5 | | kage: = TO-22 | 20 | | | | | |
| | 6 | Vol | tage rati | ng (60 = | = 600 V) | | | | |
| | 7 | • S | = D ² PA | K | | | | | |
| | _ · | | = TO-2 | - | | | | | |
| | 8 - | • N | one = tu | ibe (50 p | pieces) | | | | |
| | | • TI | RL = tap | e and re | eel (left | orienteo | d, for D ² | PAK pa | ackage) |
| | | • TI | RR = tap | be and r | eel (righ | nt orient | ed, for l | D ² PAK | package) |
| | 9 - | | | d (Pb)-fı Pb)-free | | | - | kaged | |

| ORDERING INFORMATION (Example) | | | | | | | | |
|--------------------------------|---------------------------------------|------------------------|-------------------------|--|--|--|--|--|
| PREFERRED P/N | QUANTITY PER TUBE OR TAPE AND REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | | |
| VS-HFA15TB60SPBF | 50 | 1000 | Antistatic plastic tube | | | | | |
| VS-HFA15TB60STRLP | 800 | 800 | 13" diameter reel | | | | | |
| VS-HFA15TB60STRRP | 800 | 800 | 13" diameter reel | | | | | |
| VS-HFA15TB60-1PBF | 50 | 1000 | Antistatic plastic tube | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | | |
|----------------------------|--|--|--|--|--|--|
| Dimensions | TO-263AB (D ² PAK): <u>www.vishay.com/doc?95046</u> | | | | | |
| Dimensions | TO-262AA: <u>www.vishay.com/doc?95419</u> | | | | | |
| Part marking information | TO-263AB (D ² PAK): <u>www.vishay.com/doc?95054</u> | | | | | |
| Fart marking information | TO-262AA: <u>www.vishay.com/doc?95420</u> | | | | | |
| Packaging information | www.vishay.com/doc?95032 | | | | | |
| SPICE model | www.vishay.com/doc?95357 | | | | | |

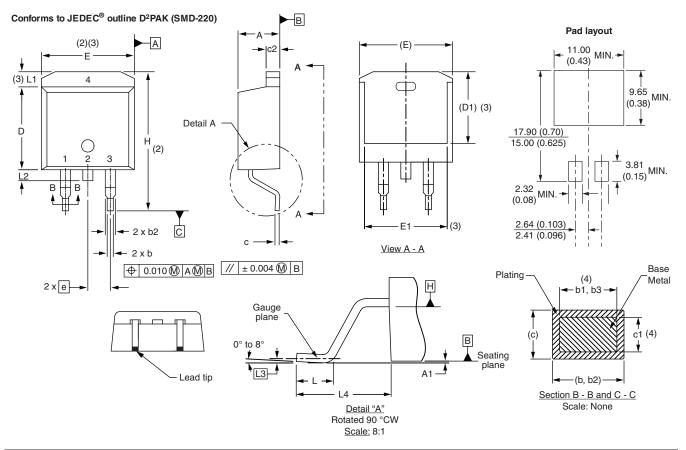
Outline Dimensions



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D²PAK

DIMENSIONS in millimeters and inches



| SYMBOL | MILLIMETERS | | INCHES | | S NOTES | | SYMBOL | MILLIN | ETERS | INC | HES | NOTES |
|--------|-------------|-------|--------|-------|---------|--|---------|--------|-------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | | STINDUL | MIN. | MAX. | MIN. | MAX. | NOTES |
| А | 4.06 | 4.83 | 0.160 | 0.190 | | | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | | E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | е | 2.54 | BSC | 0.100 |) BSC | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | Н | 14.61 | 15.88 | 0.575 | 0.625 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 1.78 | 2.79 | 0.070 | 0.110 | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | L1 | - | 1.65 | - | 0.066 | 3 |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | L2 | 1.27 | 1.78 | 0.050 | 0.070 | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | L3 | 0.25 | BSC | 0.010 |) BSC | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | L4 | 4.78 | 5.28 | 0.188 | 0.208 | |

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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1

Document Number: 95046

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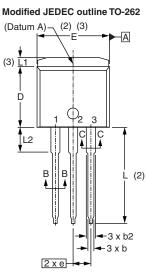


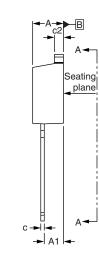
Outline Dimensions

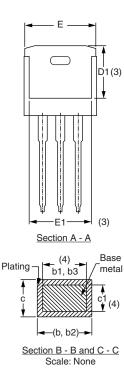
Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches







⊕0.010@A@B



| Diodes | |
|----------------------------|---------|
| 1 Anode (two die)/open (or | ne die) |
| 2., 4 Cathode | |
| 3 Anode | |

Lead assignments

Diodes

| | MILLIN | IETERS | INC | INCHES | | | |
|--------|--------|--------|-------|--------|-------|--|--|
| SYMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | | |
| А | 4.06 | 4.83 | 0.160 | 0.190 | | | |
| A1 | 2.03 | 3.02 | 0.080 | 0.119 | | | |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | |
| D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 | | |
| E | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 | | |
| E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 | | |
| e | 2.54 | BSC | 0.10 | 0 BSC | | | |
| L | 13.46 | 14.10 | 0.530 | 0.555 | | | |
| L1 | - | 1.65 | - | 0.065 | 3 | | |
| L2 | 3.56 | 3.71 | 0.140 | 0.146 | | | |

Notes

Document Number: 95419

Revision: 04-Oct-10

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body ⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

⁽⁶⁾ Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

 $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1

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